



TK11A55D(STA4,Q,M) Information



For Reference Only

Part Number TK11A55D(STA4,Q,M)

ManufacturerToshiba Semiconductor and StorageCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 550V 11A TO-220SIS

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









TK11A55D(STA4,Q,M) Specifications

Manufacturer Part Number TK11A55D(STA4,Q,M) Manufacturer Toshiba Semiconductor and Storage Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series -MOSVII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 550V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) 530V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series -MOSVII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 550V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1350pF @ 25V Vgs (Max) Land Testaure Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case TO-220SIS Package / Case	Manufacturer Part Number	TK11A55D(STA4,Q,M)
Package TO-220-3 Full Pack Series -MOSVII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 550V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Manufacturer	Toshiba Semiconductor and Storage
Package TO-220-3 Full Pack Series -MOSVII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 550V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Category	Discrete Semiconductor Products
Series -MOSVII FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 550V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case Tore Tore Tore Tore Tore Tore Tore Tor		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 550V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case	Package	TO-220-3 Full Pack
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case MOSFET (Metal Oxide) 550V MOSFET (Metal Oxide) 550V 11A (Ta) 10V 4V @ 1mA 4V @ 1mA 25nC @ 10V 1350pF @ 25V ±30V FC (TIO) 630 mOhm @ 5.5A, 10V Through Hole To-220SIS Package / Case	Series	-MOSVII
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case 11A (Ta) 10V 11A (Ta) 11A (Ta)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3 Full Pack	Drain to Source Voltage (Vdss)	550V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220SIS TO-220-3 Full Pack	Current - Continuous Drain (Id) @ 25°C	11A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case 1350pF @ 25V ±30V 630 W 630 W To-220SIS TO-220-3 Full Pack	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	25nC @ 10V
FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	1350pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 630 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	45W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	630 mOhm @ 5.5A, 10V
Supplier Device Package TO-220SIS Package / Case TO-220-3 Full Pack	Operating Temperature	150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220SIS
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

TK11A55D(STA4,Q,M) Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TK11A55D(STA4,Q,M) Payment Methods



















TK11A55D(STA4,Q,M) Shipping Methods













If you have any question about TK11A55D(STA4,Q,M), please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com